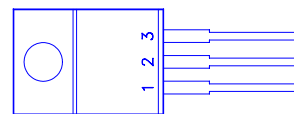
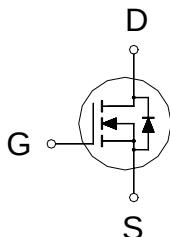


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
25	9.5m Ω	50A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	50	A
	$T_C = 100\text{ }^{\circ}\text{C}$		35	
Pulsed Drain Current ¹		I_{DM}	200	
Avalanche Current		I_{AR}	40	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	250	mJ
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	8.6	
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	65	W
	$T_C = 100\text{ }^{\circ}\text{C}$		33	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$
Lead Temperature (¹ / ₁₆ " from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3	$^{\circ}\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		70	
Case-to-Heatsink	$R_{\theta CS}$	0.7		

¹Pulse width limited by maximum junction temperature.²Duty cycle $\leq 1\%$ ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	25			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			25	μA
		V _{DS} = 20V, V _{GS} = 0V, T _C = 125 °C			250	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	50			A

Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 20A		11	16	mΩ
		V _{GS} = 10V, I _D = 25A		7.5	9.5	
Forward Transconductance ¹	g _{fs}	V _{DS} = 10V, I _D = 25A		32		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		1200	1800	pF
Output Capacitance	C _{oss}			600	1000	
Reverse Transfer Capacitance	C _{rss}			350	500	
Total Gate Charge ²	Q _g	V _{DS} = 10V, V _{GS} = 10V, I _D = 25A		25	50	nC
Gate-Source Charge ²	Q _{gs}			15		
Gate-Drain Charge ²	Q _{gd}			10		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 15V, R _L = 1Ω I _D ≅ 50A, V _{GS} = 10V, R _{GEN} = 24Ω		6	16	nS
Rise Time ²	t _r			120	250	
Turn-Off Delay Time ²	t _{d(off)}			40	90	
Fall Time ²	t _f			105	200	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _C = 25 °C)						
Continuous Current	I _S				50	A
Pulsed Current ³	I _{SM}				150	
Forward Voltage ¹	V _{SD}	I _S = 25A, V _{GS} = 0V		0.9	1.3	V
Reverse Recovery Time	t _{rr}	I _F = I _S , dI _F /dt = 100A / μS		70		nS
Peak Reverse Recovery Current	I _{RM(REC)}			200		A
Reverse Recovery Charge	Q _{rr}			0.043		μC

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

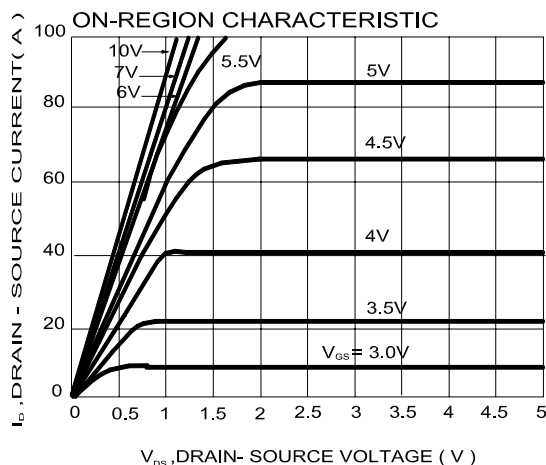
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

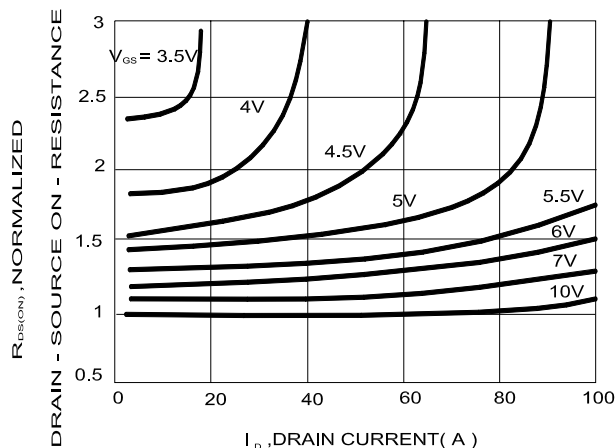
REMARK: THE PRODUCT MARKED WITH "P0903BTG", DATE CODE or LOT #

Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.

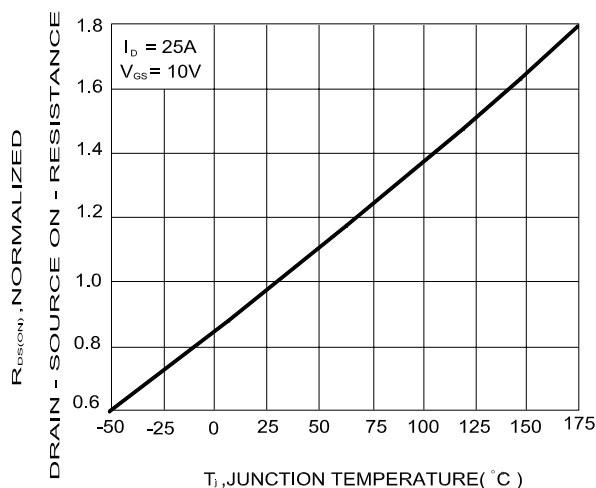
TYPICAL CHARACTERISTICS



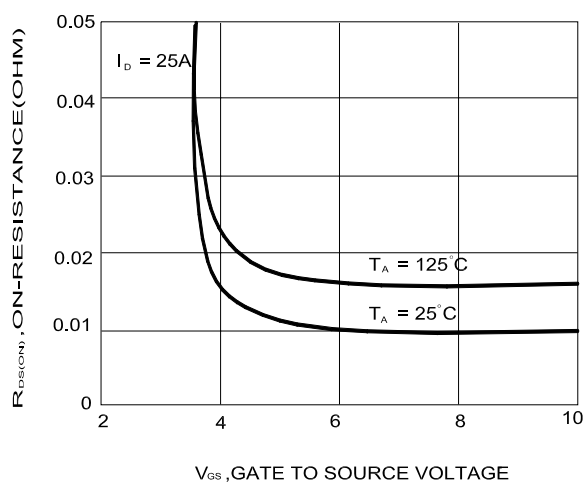
ON-RESISTANCE VARIATION WITH DRAIN CURRENT AND GATE



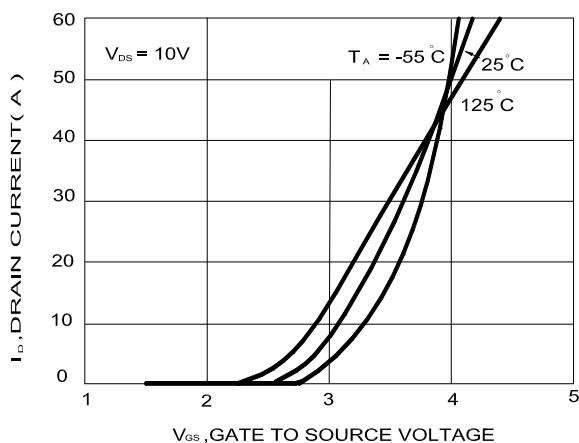
ON-RESISTANCE VARIATION WITH TEMPERATURE



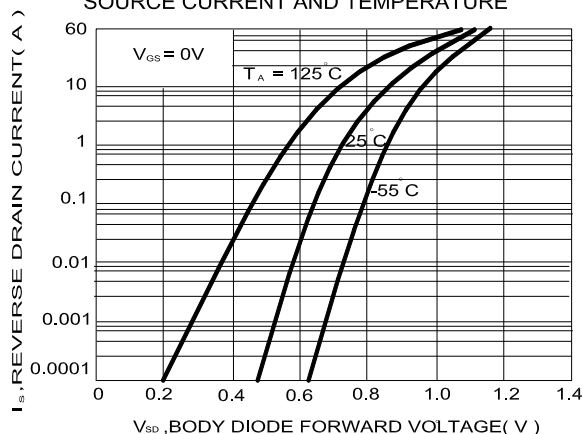
ON-RESISTANCE VARIATION WITH GATE-TO-SOURCE VOLTAGE

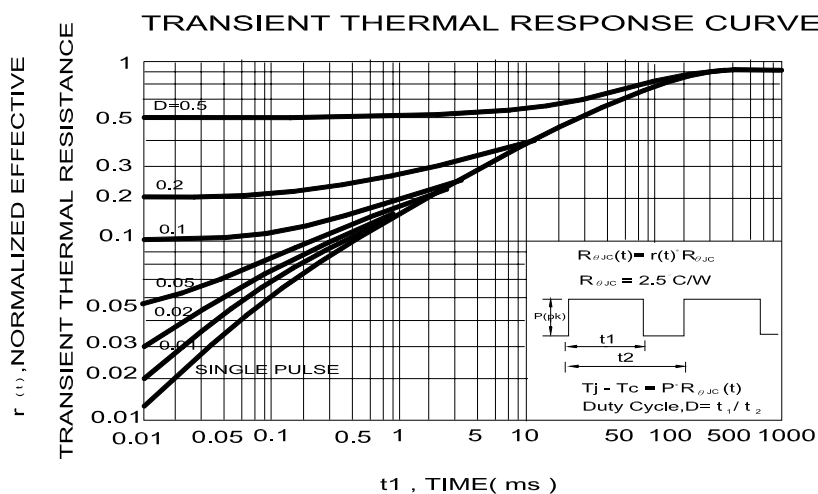
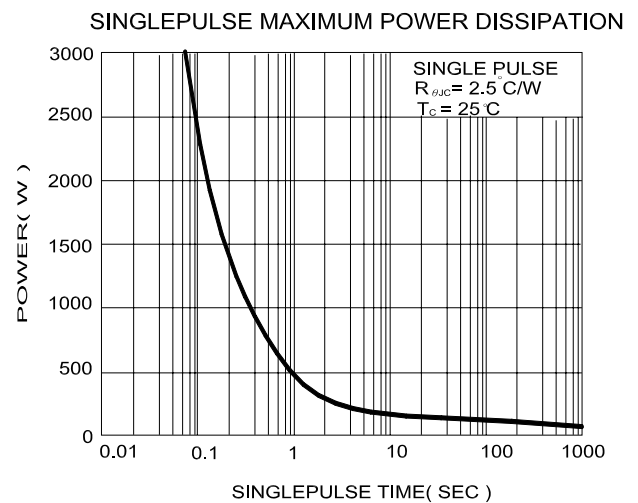
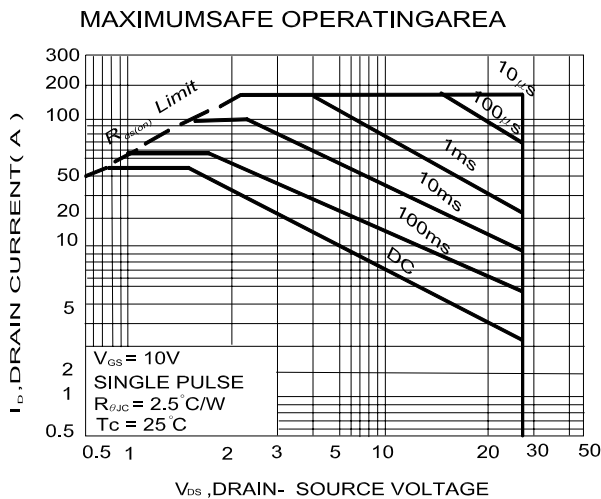
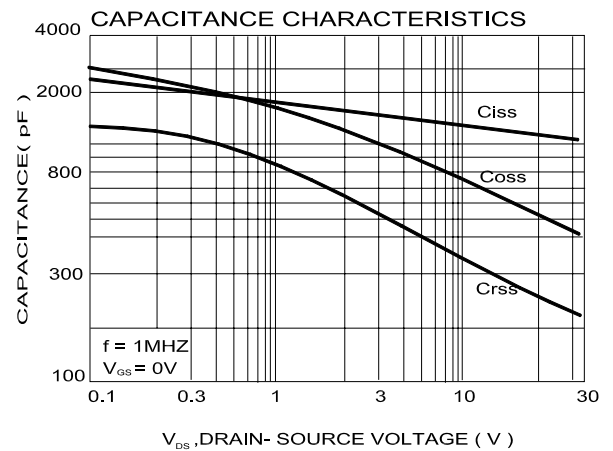
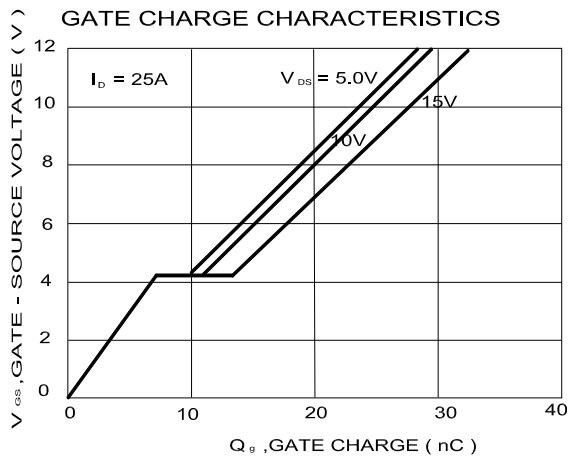


TRANSFER CHARACTERISTICS



BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE





TO-220 (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.78	10.16	10.54	H	2.4	2.54	2.68
B	2.61	2.74	2.87	I	1.19	1.27	1.35
C		20		J	4.4	4.6	4.8
D	28.5	28.9	29.3	K	1.14	1.27	1.4
E	14.6	15.0	15.4	L	2.3	2.6	2.9
F	8.4	8.8	9.2	M	0.26	0.46	0.66
G	0.72	0.8	0.88	N		7°	

